

isc Silicon NPN Power Transistor

KSD569

DESCRIPTION

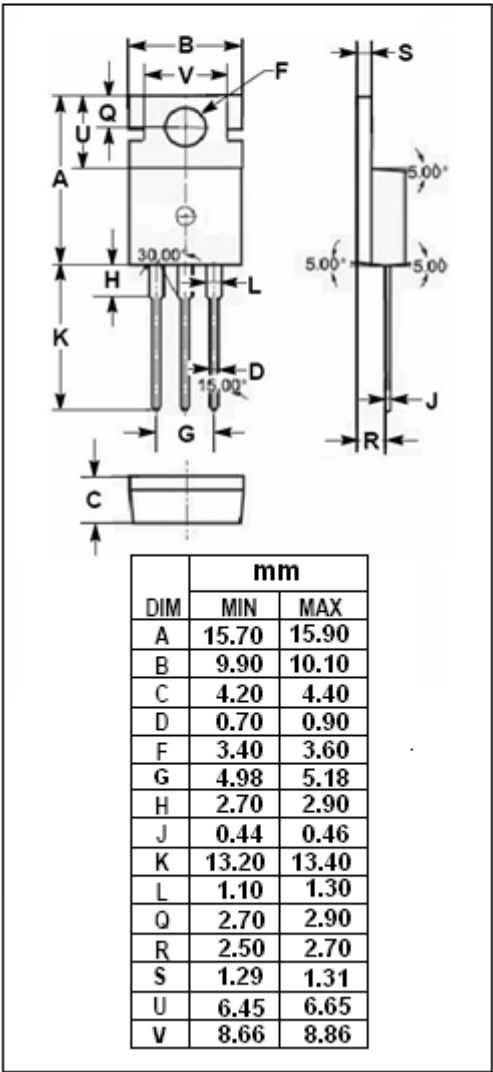
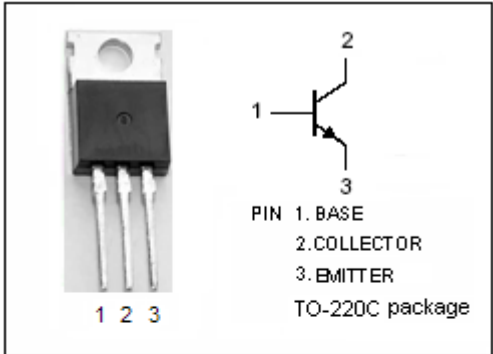
- High Collector Current:: $I_C = 7A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.5V(Max) @ I_C = 5A$
- Complement to Type KSB708

APPLICATIONS

- Designed for low-frequency power amplifiers and low-speed switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	7	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current-Continuous	3.5	A
P_C	Total Power Dissipation @ $T_C=25^{\circ}C$	40	W
	Total Power Dissipation @ $T_a=25^{\circ}C$	1.5	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**KSD569****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	80			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 80V; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μ A
h _{FE-1}	DC Current Gain	I _C = 3A; V _{CE} = 1V	40		200	
h _{FE-2}	DC Current Gain	I _C = 5A; V _{CE} = 1V	20			

◆ h_{FE-1} Classifications

R	O	Y
40-80	60-120	100-200